

Silicon Switching Diode

1N914
or
1N914-1

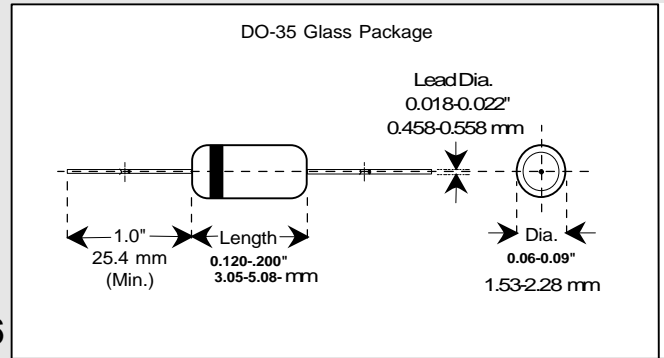
DO-35 Glass Package

Applications

Used in general purpose applications, where performance and switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/116
- Available up to JANTXV levels
- "S" level screening available to SCDs



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	100 (Min.)	Volts
Average Rectified Current	I_{Avg}	75	mAmps
Continuous Forward Current	I_{Fdc}	300	mAmps
Peak Surge Current ($t_{peak} = 1 \text{ sec.}$)	I_{peak}	0.5	Amp
Power Dissipation @ $T_L = 50 \text{ }^\circ\text{C}$, $L = 3/8"$ from body	P_{tot}	250	mWatts
Storage & Operating Temperature Range	$T_{St \& Op}$	-65 to +200	$^\circ\text{C}$

Electrical Characteristics @ 25 $^\circ\text{C}$ *	Symbol	Absolute Limits	Unit
Breakdown Voltage @ $I_r = 0.1 \text{ mA}$	PIV	100 (Min)	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	I_R	0.025 (Max)	μA
Reverse Leakage ($V_r = 20 \text{ V}$, $150 \text{ }^\circ\text{C}$)	I_R	50 (Max)	μA
Reverse Leakage Current @ $V_R = 75 \text{ V}$	I_R	5.0 (Max)	μA
Capacitance @ $V_R = 0 \text{ V}$, $f = 1\text{MHz}$	C_T	4.0 (Max)	pF
Reverse Recovery Time (note 1)	t_{rr}	4.0 (Max)	nSecs
Forward Recovery Time (note 2)	V_{fr}	2.5 (Max)	Volts

Note 1: $I_F = 10 \text{ mA}$, $R_L = 100 \text{ Ohms}$, $V_r = 6.0 \text{ Volts}$, $I_{rr} = 1.0 \text{ mA}$

Note 2: $I_F = 50 \text{ mA dc}$

***UNLESS OTHERWISE SPECIFIED**



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